

BIPOLAR ANALOG INTEGRATED CIRCUIT $\mu PC4570$

ULTRA LOW-NOISE, WIDEBAND, DUAL OPERATIONAL AMPLIFIER

DESCRIPTION

The μ PC4570 is an ultra low-noise, wideband high slew-rate, dual operational amplifier. Input equivalent noise is three times better than the conventional 4558 type op-amps. The gain bandwidth products and the slew-rate are seven times better than 4558. In spite of fast AC performance, the μ PC4570 is extremely stable under voltage-follower circuit conditions. Supply current is also improved compared with conventional wideband op-amps. The μ PC4570 is an excellent choice for pre-amplifiers and active filters in audio, instrumentation, and communication circuits.

FEATURES

• Ultra low noise : $e_n = 4.5 \text{ nV}/\sqrt{\text{Hz}}$

High slew rate : 7 V/μs

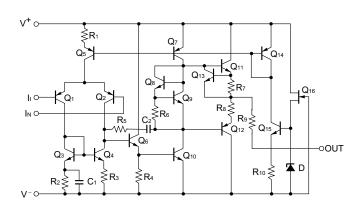
• High gain bandwidth product : GBW = 15 MHz at 100 kHz

• Internal frequency compensation

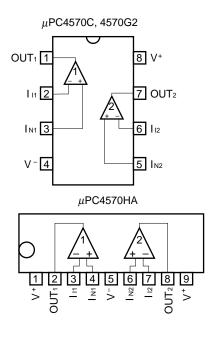
ORDERING INFORMATION

Part Number	Package
μPC4570C	8-pin plastic DIP (7.62 mm (300))
μ PC4570G2	8-pin plastic SOP (5.72 mm (225))
μ PC4570HA	9-pin plastic slim SIP
μPC4570G2	8-pin plastic SOP (5.72 mm (225))

EQUIVALENT CIRCUIT (1/2 Circuit)



PIN CONFIGURATION (Top View)



The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version. Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Parameter		Symbol	Ratings	Unit
Voltage between V ⁺ a	nd V ^{- Note 1}	V* - V	-0.3 to +36	V
Differential Input Volta	ge	VID	±30	V
Input Voltage Note 2		Vı	√-0.3 to V ⁺ +0.3	V
Output Voltage Note 3		Vo	√-0.3 to V ⁺ +0.3	V
Power Dissipation	Note 4		350	mW
	G2 Package Note 5		440	mW
HA Package Note 4			350	mW
Output Short Circuit D			10	sec
Operating Ambient Temperature		Та	-20 to +80	°C
Storage Temperature		Tstg	-55 to +125	°C

- **Notes 1.** Reverse connection of supply voltage can cause destruction.
 - 2. The input voltage should be allowed to input without damage or destruction. Even during the transition period of supply voltage, power on/off etc., this specification should be kept. The normal operation will establish when the both inputs are within the Common Mode Input Voltage Range of electrical characteristics.
 - 3. This specification is the voltage which should be allowed to supply to the output terminal from external without damage or destruction. Even during the transition period of supply voltage, power on/off etc., this specification should be kept. The output voltage of normal operation will be the Output Voltage Swing of electrical characteristics.
 - 4. Thermal derating factor is -5.0 mW/°C when operating ambient temperature is higher than 55°C.
 - 5. Thermal derating factor is -4.4 mW/°C when operating ambient temperature is higher than 25°C.
 - **6.** Pay careful attention to the total power dissipation not to exceed the absolute maximum ratings, Note 4 and Note 5.

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply Voltage	V [±]	<u>±</u> 4		±16	V
Output Current	lo			±10	mA
Source Resistance	Rs			50	kΩ
Capacitive Load (Av = +1)	C∟			100	pF



ELECTRICAL CHARACTERISTICS (TA = 25°C, V^{\pm} = ±15 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input Offset Voltage	Vio	Rs ≤ 50 Ω		±0.3	±5	mV
Input Offset Current Note	lio			±10	±100	nA
Input Bias Current Note	lв			100	400	nA
Large Signal Voltage Gain	Av	$R_L \ge 2 \text{ k}\Omega$, $V_0 = \pm 10 \text{ V}$	30,000	300,000		
Supply Current	Icc	lo = 0 A, Both Amplifiers		5	8	mA
Common Mode Rejection Ratio	CMR		80	100		dB
Supply Voltage Rejection Ratio	SVR		80	100		dB
Output Voltage Swing	Vom	$R_L \ge 10 \text{ k}\Omega$	±12	±13.4		V
		$R_L \ge 2 k\Omega$	±10	±12.8		V
Common Mode Input Voltage Range	Vісм		±12	±14		V
Slew Rate	SR	$R_L \ge 2 k\Omega$	5	7		V/μs
Gain Bandwidth Product	GBW	fo = 100 kHz	10	15		MHz
Unity Gain Frequency	funity	open loop		7		MHz
Phase Margin	$oldsymbol{\phi}$ unity	open loop		50		degree
Total Harmonic Distortion	THD	Vo = 3 Vr.m.s., f = 20 Hz to		0.002		%
		20 kHz (Figure1)				
Input Equivalent Noise Voltage	Vn	RIAA (Figure2)		0.9		$\mu V_{r.m.s.}$
		FLAT+JIS A, Rs = 100Ω		0.53	0.65	$\mu V_{r.m.s.}$
		(Figure3)				
Input Equivalent Noise Voltage Density	e n	fo = 10 Hz, Rs = 100 Ω		5.5		nV/√Hz
		fo = 1 kHz, Rs = 100 Ω		4.5		nV/√ Hz
Input Equivalent Noise Current Density	İn	fo = 1 kHz		0.7		pA/√Hz
Channel Separation		f = 20 Hz to 20 kHz		120		dB

Note Input bias currents flow out from IC. Because each currents are base current of PNP-transistor on input stage.

Data Sheet G10528EJ6V0DS 3

MEASUREMENT CIRCUIT

Figure 1 Total Harmonic Distortion Measurement Circuit

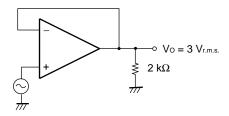


Figure 2 Noise Measurement Circuit (RIAA)

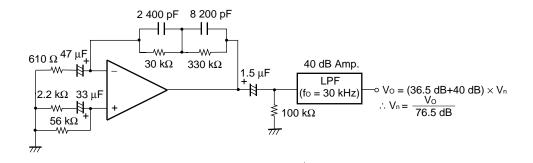
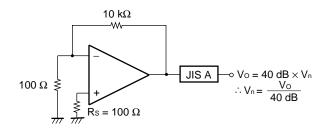
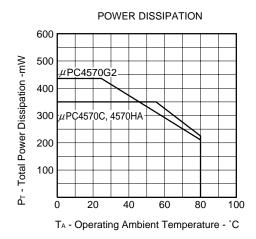


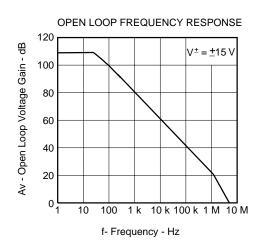
Figure 3 Noise Measurement Circuit (FLAT+JIS A)

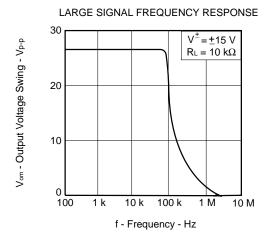


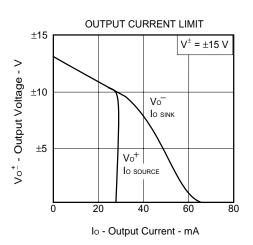
4

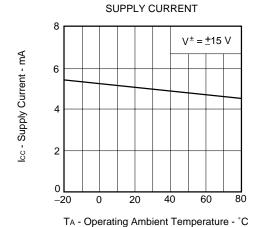
TYPICAL PERFORMANCE CHARACTERISTICS (TA = 25°C, TYP.)

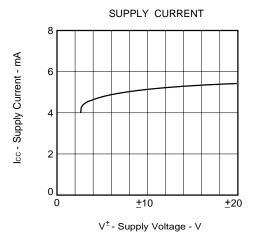






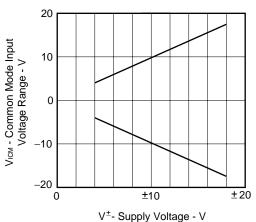




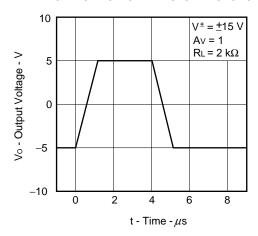


Data Sheet G10528EJ6V0DS

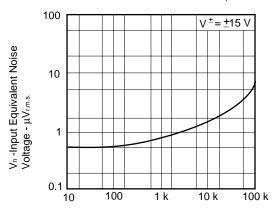
COMMON MODE INPUT VOLTAGE RANGE



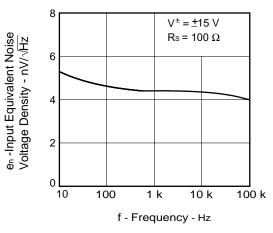
VOLTAGE FOLLOWER PULSE RESPONSE



INPUT EQUIVALENT NOISE VOLTAGE (FLAT+JIS A)

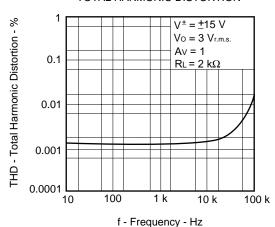


INPUT EQUIVALENT NOISE VOLTAGE DENSITY



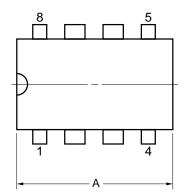
TOTAL HARMONIC DISTORTION

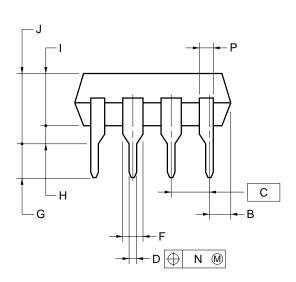
 \mbox{Rs} - Source Resistance - Ω

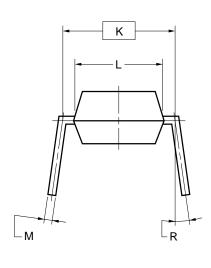


★ PACKAGE DRAWINGS (Unit: mm)

8-PIN PLASTIC DIP (7.62mm(300))







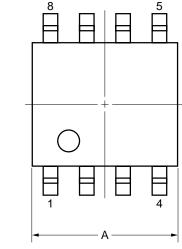
NOTES

- 1. Each lead centerline is located within 0.25 mm of its true position (T.P.) at maximum material condition.
- 2. Item "K" to center of leads when formed parallel.

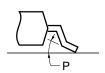
ITEM	MILLIMETERS		
Α	10.16 MAX.		
В	1.27 MAX.		
С	2.54 (T.P.)		
D	0.50±0.10		
F	1.4 MIN.		
G	3.2±0.3		
Н	0.51 MIN.		
I	4.31 MAX.		
J	5.08 MAX.		
K	7.62 (T.P.)		
L	6.4		
М	$0.25^{+0.10}_{-0.05}$		
N	0.25		
Р	0.9 MIN.		
R	0~15°		

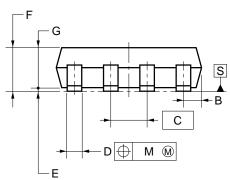
P8C-100-300B,C-2

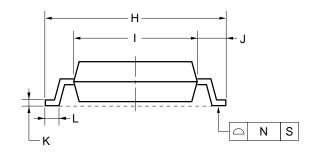
8-PIN PLASTIC SOP (5.72 mm (225))



detail of lead end







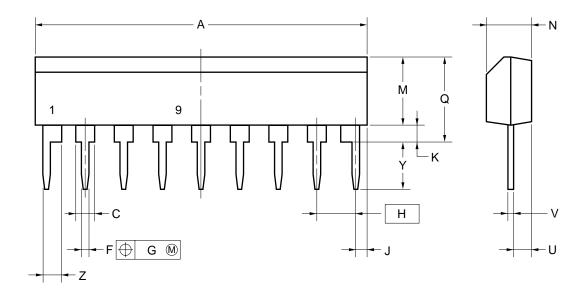
NOTE

Each lead centerline is located within 0.12 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
Α	$5.2_{-0.20}^{+0.17}$
В	0.78 MAX.
С	1.27 (T.P.)
D	$0.42^{+0.08}_{-0.07}$
Е	0.1±0.1
F	1.59±0.21
G	1.49
Н	6.5±0.3
- 1	4.4±0.15
J	1.1±0.2
K	$0.17^{+0.08}_{-0.07}$
L	0.6±0.2
М	0.12
N	0.10
Р	3°+7°

S8GM-50-225B-6

9-PIN PLASTIC SLIM SIP



NOTE

Each lead centerline is located within 0.25 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
Α	22.86 MAX.
С	1.1 MIN.
F	0.5±0.1
G	0.25
Н	2.54
J	1.27 MAX.
K	0.51 MIN.
М	5.08 MAX.
N	2.8±0.2
Q	5.75 MAX.
U	1.5 MAX.
V	$0.25^{+0.10}_{-0.05}$
Υ	3.2±0.5
Z	1.1 MIN.
	DOLLA OF AD A

P9HA-254B-2

★ RECOMMENDED SOLDERING CONDITIONS

When soldering this product, it is highly recommended to observe the conditions as shown below. If other soldering processes are used, or if the soldering is performed under different conditions, please make sure to consult with our sales offices.

For more details, refer to our document "SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL" • (C10535E).

Type of Surface Mount Device

μPC4570G2: 8-pin plastic SOP (5.72 mm (225))

Process	Conditions	Symbol
Infrared Ray Reflow	Peak temperature: 230°C or below (Package surface temperature),	IR30-00-1
	Reflow time: 30 seconds or less (at 210°C or higher),	
	Maximum number of reflow processes: 1 time.	
Vapor Phase Soldering	Peak temperature: 215°C or below (Package surface temperature),	VP15-00-1
	Reflow time: 40 seconds or less (at 200°C or higher),	
	Maximum number of reflow processes: 1 time.	
Wave Soldering	Solder temperature: 260°C or below, Flow time: 10 seconds or less,	WS60-00-1
	Maximum number of flow processes: 1 time,	
	Pre-heating temperature: 120°C or below (Package surface temperature).	
Partial Heating Method	Pin temperature: 300°C or below,	_
	Heat time: 3 seconds or less (Per each side of the device).	

Caution Apply only one kind of soldering condition to a device, except for "partial heating method", or the device will be damaged by heat stress.

Type of Through-hole Device

 μ PC4570C: 8-pin plastic DIP (7.62 mm (300)), μ PC4570HA: 9-pin plastic slim SIP

Process	Conditions	
Wave Soldering	Solder temperature: 260°C or below,	
(only to leads)	Flow time: 10 seconds or less.	
Partial Heating Method	Pin temperature: 300°C or below,	
	Heat time: 3 seconds or less (per each lead).	

Caution For through-hole device, the wave soldering process must be applied only to leads, and make sure that the package body does not get jet soldered.

NEC μ PC4570

[MEMO]

- The information in this document is current as of October, 2001. The information is subject to change without notice. For actual design-in, refer to the latest publications of NEC's data sheets or data books, etc., for the most up-to-date specifications of NEC semiconductor products. Not all products and/or types are available in every country. Please check with an NEC sales representative for availability and additional information.
- No part of this document may be copied or reproduced in any form or by any means without prior written consent of NEC. NEC assumes no responsibility for any errors that may appear in this document.
- NEC does not assume any liability for infringement of patents, copyrights or other intellectual property rights of
 third parties by or arising from the use of NEC semiconductor products listed in this document or any other
 liability arising from the use of such products. No license, express, implied or otherwise, is granted under any
 patents, copyrights or other intellectual property rights of NEC or others.
- Descriptions of circuits, software and other related information in this document are provided for illustrative
 purposes in semiconductor product operation and application examples. The incorporation of these
 circuits, software and information in the design of customer's equipment shall be done under the full
 responsibility of customer. NEC assumes no responsibility for any losses incurred by customers or third
 parties arising from the use of these circuits, software and information.
- While NEC endeavours to enhance the quality, reliability and safety of NEC semiconductor products, customers
 agree and acknowledge that the possibility of defects thereof cannot be eliminated entirely. To minimize
 risks of damage to property or injury (including death) to persons arising from defects in NEC
 semiconductor products, customers must incorporate sufficient safety measures in their design, such as
 redundancy, fire-containment, and anti-failure features.
- NEC semiconductor products are classified into the following three quality grades:
 "Standard", "Special" and "Specific". The "Specific" quality grade applies only to semiconductor products
 developed based on a customer-designated "quality assurance program" for a specific application. The
 recommended applications of a semiconductor product depend on its quality grade, as indicated below.
 Customers must check the quality grade of each semiconductor product before using it in a particular
 - "Standard": Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots
 - "Special": Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)
 - "Specific": Aircraft, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems and medical equipment for life support, etc.

The quality grade of NEC semiconductor products is "Standard" unless otherwise expressly specified in NEC's data sheets or data books, etc. If customers wish to use NEC semiconductor products in applications not intended by NEC, they must contact an NEC sales representative in advance to determine NEC's willingness to support a given application.

(Note)

application.

- (1) "NEC" as used in this statement means NEC Corporation and also includes its majority-owned subsidiaries.
- (2) "NEC semiconductor products" means any semiconductor product developed or manufactured by or for NEC (as defined above).

M8E 00.4